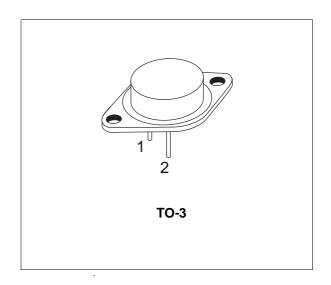


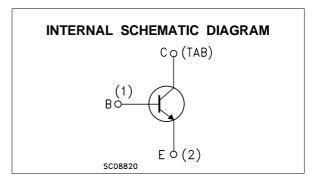
HIGH POWER NPN SILICON TRANSISTOR

 STMicroelectronics PREFERRED SALESTYPES

DESCRIPTION

The 2N3771, 2N3772 are silicon epitaxial-base NPN transistors mounted in Jedec Jedec TO-3 metal case. They are intended for linear amplifiers and inductive switching applications.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Va	Unit	
		2N3771	2N3772	
V_{CEO}	Collector-Emitter Voltage (I _E = 0)	40	60	V
V _{CEV}	Collector-Emitter Voltage (V _{BE} = -1.5V)	50	80	V
Vсво	Collector-Base Voltage (I _B = 0)	50	100	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	5	7	V
Ic	Collector Current	30	20	Α
I _{CM}	Collector Peak Current	30	30	Α
I _B	Base Current	7.5	5	Α
I _{BM}	Base Peak Current	15	15	Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C	150		W
T _{stg}	Storage Temperature	-65 to	°C	

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THERMAL DATA

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

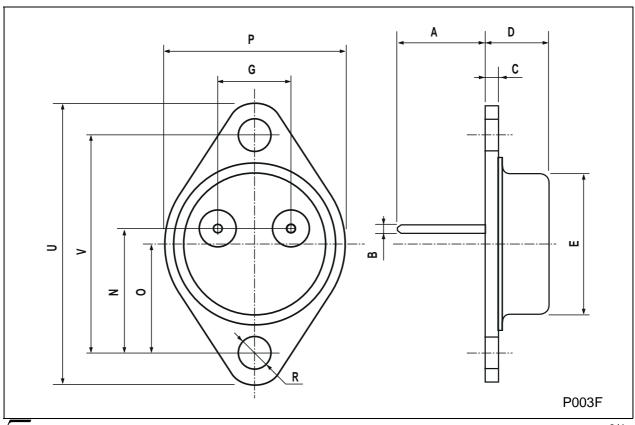
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)				2 5 10	mA mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	for 2N3771 V _{CB} = 30 V for 2N3772 V _{CB} = 50 V			10 10	mA mA
I _{CBO}	Collector Cut-off Current (I _E = 0)	for 2N3771 V _{CB} = 50 V for 2N3772 V _{CB} = 100 V			4 5	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	for 2N3771 V _{CB} = 5 V for 2N3772 V _{CB} = 7 V			5 5	mA mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 0.2 A for 2N3771 for 2N3772	40 60			V V
V _{CEV(sus)} *	Collector-Emitter Sustaining Voltage (V _{EB} = -1.5V)	I_C = 0.2 A R_{BE} = 100 Ω for 2N3771 for 2N3772	50 80			V V
V _{CER(sus)} *	Collector-Emitter Sustaining Voltage (R _{BE} = 100 Ω)	I _C = 0.2 A for 2N3771 for 2N3772	45 70			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	for 2N3771 C = 15 A			2 4 1.4 4	V V V
V _{BE} *	Base-Emitter Voltage	I _C = 20 A I _B = 4 A for 2N3771 I _C = 15 A V _{CE} = 4 V for 2N3772 I _C = 10 A V _{CE} = 4 A			2.7	V
h _{FE} *	DC Current Gain	for 2N3771 IC = 15 A	15 5		60	
		Ic = 10 A V _{CE} = 4 V Ic = 20 A V _{CE} = 4 V	15 5		60	
h _{FE}	Small Signal Current Gain	Ic = 1 A	40			
f _T	Transition frequency	I _C = 1 A V _{CE} = 4 V f = 50 KHz	0.2			MHz
I _{s/b}	Second Breakdown Collector Current	V _{CE} = 25 V t = 1 s (non repetitive)	6			Α

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	0.97		1.15	0.038		0.045
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
Е	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



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